

MEMORY Mobile FCRAM™

CMOS

16 Mbit (1 M word × 16 bit) Mobile Phone Application Specific Memory

MB82D01171A-80/80L/80LL/85/85L/85LL/90/90L/90LL

CMOS 1,048,576-WORD × 16 BIT
Fast Cycle Random Access Memory
with Low Power SRAM Interface

DESCRIPTION

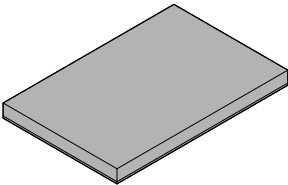
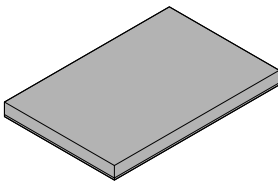
The Fujitsu MB82D01171A is a CMOS Fast Cycle Random Access Memory (FCRAM) with asynchronous Static Random Access Memory (SRAM) interface containing 16,777,216 storages accessible in a 16-bit format. This MB82D01171A is suited for low power applications such as Cellular Handset and PDA.

Note: FCRAM is a trademark of Fujitsu Limited, Japan.

PRODUCT LINEUP

Parameter	MB82D01171A								
	80	80L	80LL	85	85L	85LL	90	90L	90LL
Access Time (t _{AA} Max, t _{CE} Max)	80 ns			85 ns			90 ns		
Active Current (I _{DDA1} Max)	20 mA								
Standby Current (I _{DDs1} Max)	200 μA	100 μA	70 μA	200 μA	100 μA	70 μA	200 μA	100 μA	70 μA
Power Down Current (I _{DDP} Max)	10 μA								

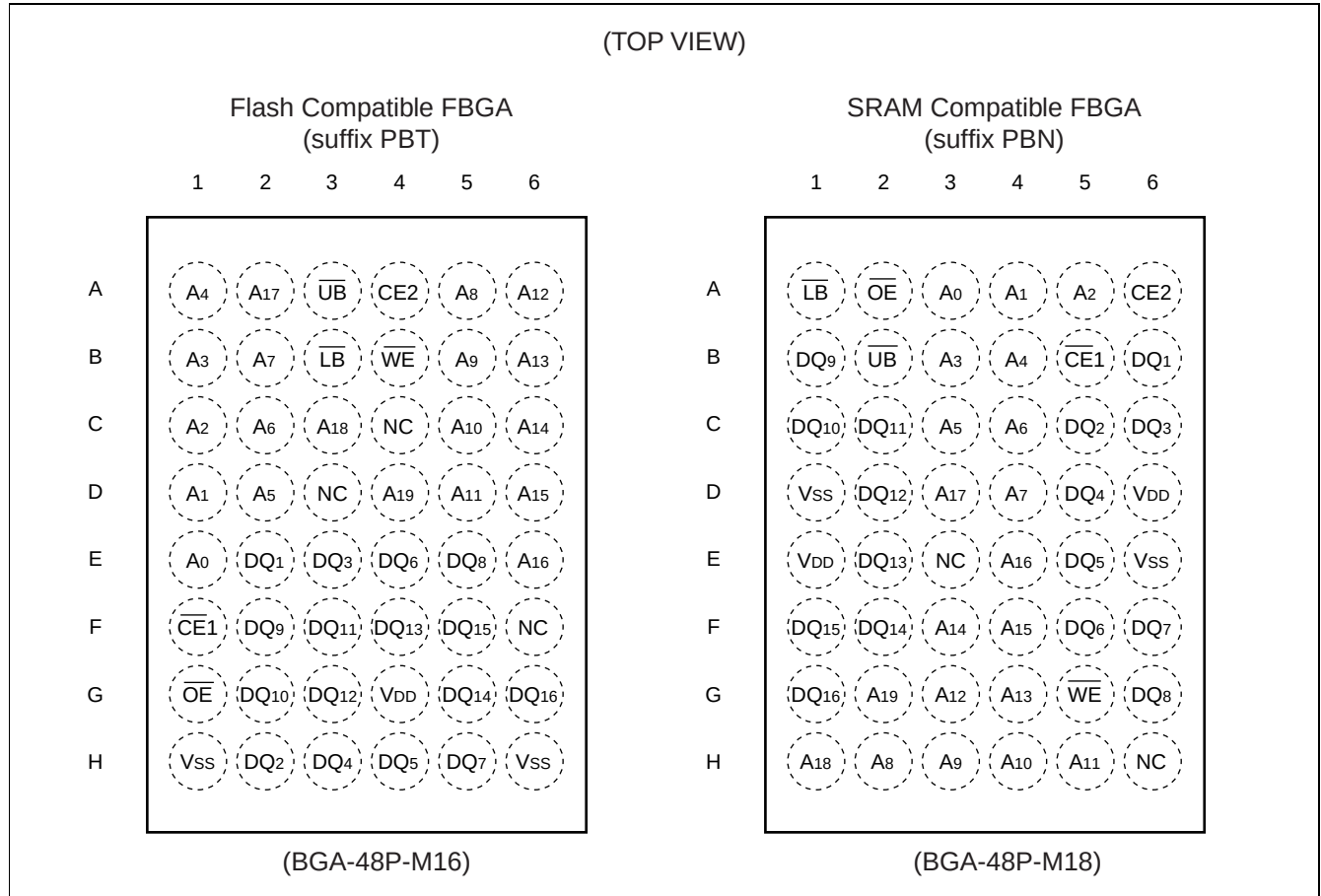
PACKAGES

48-ball plastic FBGA	48-ball plastic FBGA
	
(BGA-48P-M16)	(BGA-48P-M18)

■ FEATURES

- Asynchronous SRAM Interface
- 1 M word × 16 bit Organization
- Fast Random Cycle Time : $t_{RC} = 90 \text{ ns}$
- Fast Random Access Time : $t_{AA} = t_{CE} = 80 \text{ ns}, 85 \text{ ns}, 90 \text{ ns}$
- Low Power Consumption : $I_{DDSI} = 200 \mu\text{A}, 100 \mu\text{A} \text{ (L version)}, 70 \mu\text{A} \text{ (LL version)}$
- Wide Operating Conditions : $V_{DD} = +2.3 \text{ V to } +2.7 \text{ V}$
 $+2.7 \text{ V to } +3.1 \text{ V}$
 $+3.1 \text{ V to } +3.5 \text{ V}$
 $T_A = -30 \text{ }^\circ\text{C to } +85 \text{ }^\circ\text{C}$
- Byte Write Control
- 4 words Address Access Capability
- Power Down Control by CE2

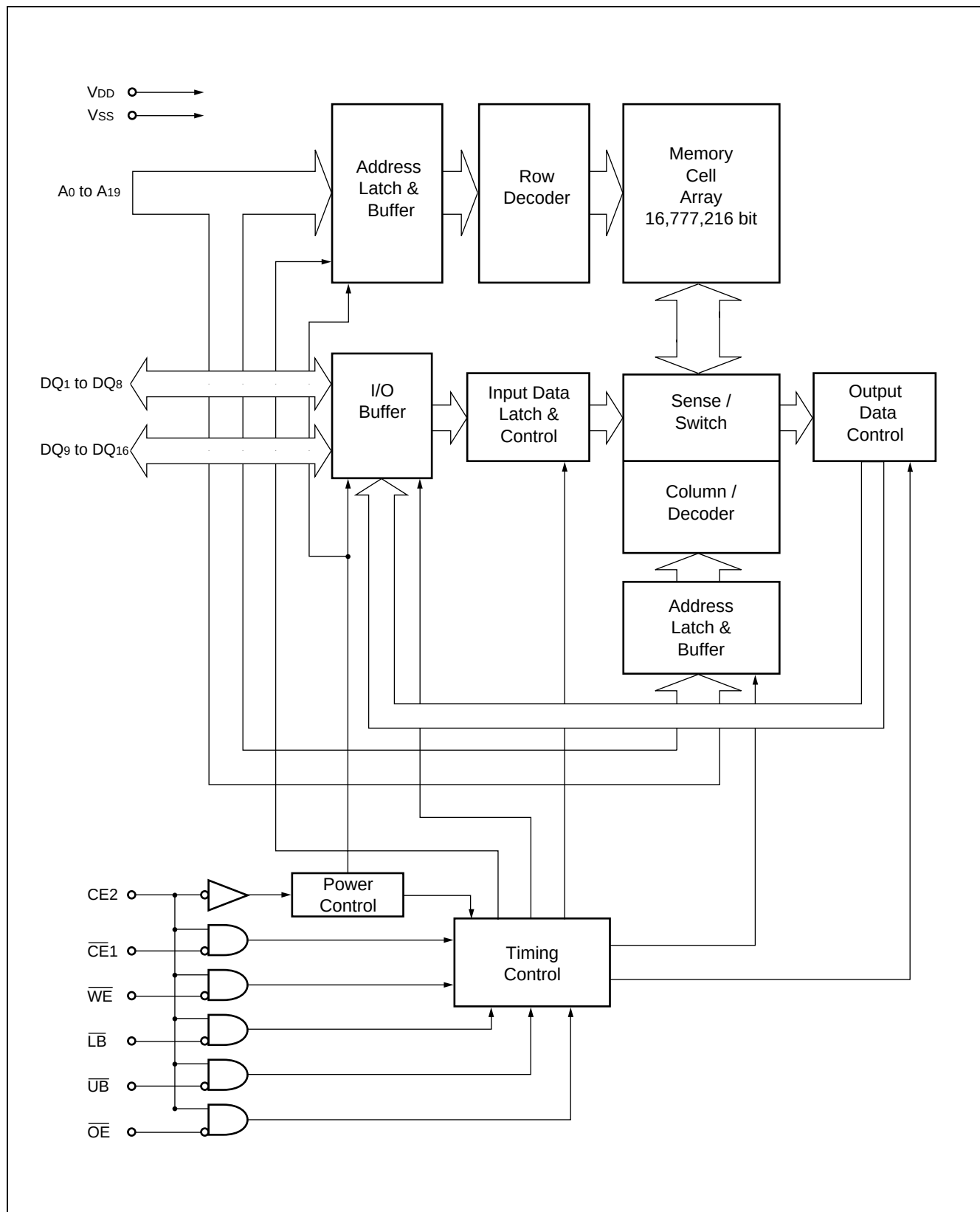
PIN ASSIGNMENTS



PIN DESCRIPTION

Pin Name	Description
A ₀ to A ₁₉	Address Input
$\overline{CE1}$	Chip Enable (Low Active)
CE2	Chip Enable (High Active)
$\overline{WE}$	Write Enable (Low Active)
$\overline{OE}$	Output Enable (Low Active)
$\overline{LB}$	Lower Byte Write Control (Low Active)
$\overline{UB}$	Upper Byte Write Control (Low Active)
DQ ₁ to DQ ₈	Lower Byte Data Input/Output
DQ ₉ to DQ ₁₆	Upper Byte Data Input/Output
V _{DD}	Power Supply
V _{SS}	Ground
NC	No Connection

■ BLOCK DIAGRAM



■ FUNCTION TRUTH TABLE *1

Mode	$\overline{\text{CE}}1$	CE2	$\overline{\text{WE}}$	$\overline{\text{OE}}$	$\overline{\text{LB}}$	$\overline{\text{UB}}$	DQ ₁ to DQ ₈	DQ ₉ to DQ ₁₆	I _{DD}	Data Retention
Power Down *2	X	L	X	X	X	X	High-Z	High-Z	I _{DDP}	No
Standby (Deselect)	H	H	X	X	X	X	High-Z	High-Z	I _{DDS}	Yes
Output Disable*3	L		H	H	X	X	High-Z	High-Z	I _{DDA}	
Read*4				L	X	X	Output Valid	Output Valid		
Write			L	H	L	L	Input Valid	Input Valid		
Write (Lower Byte)					L	H	Input Valid	Invalid		
Write (Upper Byte)					H	L	Invalid	Input Valid		

*1 : V = Valid, L = Logic Low, H = Logic High, X = either "L" or "H", High-Z = High Impedance

*2 : Power Down mode can be entered from Standby state and all DQ pins are in High-Z state.

*3 : Output Disable mode should not be kept longer than 1 μ s.

*4 : Byte control at Read mode is not supported.

■ ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Rating		Unit
		Min	Max	
Voltage of V _{DD} Supply Relative to V _{SS}	V _{DD}	−0.5	+3.6	V
Voltage at Any Pin Relative to V _{SS}	V _{IN}	−0.5	+3.6	V
	V _{OUT}	−0.5	+3.6	V
Short Circuit Output Current	I _{OUT}	−50	+50	mA
Storage Temperature	T _{STG}	−55	+125	°C

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

■ RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Value		Unit
		Min	Max	
Supply Voltage *1	V _{DD} (31)	3.1	3.5	V
	V _{DD} (27)	2.7	3.1	V
	V _{DD} (23)	2.3	2.7	V
	V _{SS}	0	0	V
High Level Input Voltage *1, *2	V _{IH} (31)	2.6	V _{DD} + 0.3 and ≤ 3.6	V
	V _{IH} (27)	2.2	V _{DD} + 0.3	V
	V _{IH} (23)	2.0	V _{DD} + 0.3	V
Low Level Input Voltage *1, *2	V _{IL} (31)	−0.3	0.5	V
	V _{IL} (27)	−0.3	0.5	V
	V _{IL} (23)	−0.3	0.4	V
Ambient Temperature	T _A	−30	85	°C

*1 : All voltages are referenced to V_{SS}.

*2 : Minimum DC voltage on input or I/O pins are −0.3 V. During voltage transitions, inputs may undershoot V_{SS} to −1.0 V for periods of up to 5 ns. Maximum DC voltage on input and I/O pins are V_{DD} + 0.3 V.

During voltage transitions, inputs may positive overshoot to V_{DD} + 1.0 V for periods of up to 5 ns.

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representatives beforehand.

MB82D01171A-80/80L/80LL/85/85L/85LL/90/90L/90LL

PIN CAPACITANCE

(f = 1.0 MHz, T_A = +25 °C)

Parameter	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Address Input Capacitance	C _{IN1}	V _{IN} = 0 V	—	—	5	pF
Control Input Capacitance	C _{IN2}	V _{IN} = 0 V	—	—	5	pF
Data Input/Output Capacitance	C _{IO}	V _{IO} = 0 V	—	—	8	pF

ELECTRICAL CHARACTERISTICS

1. DC Characteristics

Parameter	Symbol	Conditions	Value		Unit
			Min	Max	
Input Leakage Current	I _{LI}	V _{SS} ≤ V _{IN} ≤ V _{DD}	−1.0	+1.0	μA
Output Leakage Current	I _{LO}	0 V ≤ V _{OUT} ≤ V _{DD} , Output Disable	−1.0	+1.0	μA
Output High Voltage Level	V _{OH(31)}	V _{DD} = V _{DD(31)} , I _{OH} = −0.5 mA	2.4	—	V
	V _{OH(27)}	V _{DD} = V _{DD(27)} , I _{OH} = −0.5 mA	2.25	—	V
	V _{OH(23)}	V _{DD} = V _{DD(23)} , I _{OH} = −0.5 mA	1.8	—	V
Output Low Voltage Level	V _{OL}	I _{OL} = 1 mA	—	0.4	V
V _{DD} Power Down Current	I _{DDP}	V _{DD} = V _{DD(31)} Max, V _{IN} = V _{IH} or V _{IL} , CE2 ≤ 0.2 V	—	20	μA
		V _{DD} = V _{DD(27, 23)} Max, V _{IN} = V _{IH} or V _{IL} , CE2 ≤ 0.2 V	—	10	μA
V _{DD} Standby Current	L Version LL Version	I _{DDS} V _{DD} = V _{DD(31)} Max, V _{IN} = V _{IH} or V _{IL} CE1 = CE2 = V _{IH} , I _{OUT} = 0 mA	—	5.5	mA
			—	2.0	
			—	1.5	
	L Version LL Version	I _{DDS} V _{DD} = V _{DD(27, 23)} Max, V _{IN} = V _{IH} or V _{IL} CE1 = CE2 = V _{IH} , I _{OUT} = 0 mA	—	5	mA
			—	1.5	
			—	1	
	L Version LL Version	I _{DDSD1} V _{DD} = V _{DD(31)} Max, V _{IN} ≤ 0.2 V or V _{IN} ≥ V _{DD} − 0.2 V, CE1 = CE2 ≥ V _{DD} − 0.2 V, I _{OUT} = 0 mA	—	250	μA
			—	150	
			—	120	
	L Version LL Version	I _{DDSD1} V _{DD} = V _{DD(27, 23)} Max, V _{IN} ≤ 0.2 V or V _{IN} ≥ V _{DD} − 0.2 V, CE1 = CE2 ≥ V _{DD} − 0.2 V, I _{OUT} = 0 mA	—	200	μA
			—	100	
			—	70	

(Continued)

(Continued)

Parameter	Symbol	Conditions	Value		Unit
			Min	Max	
V _{DD} Active Current	I _{DDA1}	V _{DD(31)} = V _{DD} Max, V _{IN} = V _{IH} or V _{IL} , $\overline{\text{CE1}}$ = V _{IL} and CE2 = V _{IH} , I _{OUT} = 0 mA	—	25	mA
		V _{DD(27, 23)} = V _{DD} Max, V _{IN} = V _{IH} or V _{IL} , $\overline{\text{CE1}}$ = V _{IL} and CE2 = V _{IH} , I _{OUT} = 0 mA		20	
	I _{DDA2}	V _{DD(31)} = V _{DD} Max, V _{IN} = V _{IH} or V _{IL} , $\overline{\text{CE1}}$ = V _{IL} and CE2 = V _{IH} , I _{OUT} = 0 mA	—	4.0	mA
		V _{DD(27, 23)} = V _{DD} Max, V _{IN} = V _{IH} or V _{IL} , $\overline{\text{CE1}}$ = V _{IL} and CE2 = V _{IH} , I _{OUT} = 0 mA		3.0	

- Notes:
- All voltages are referenced to V_{SS}.
 - DC Characteristics are measured after following POWER-UP timing.
 - I_{OUT} depends on the output load conditions.

2. AC Characteristics

(1) Read Operation

Parameter	Symbol	-80/-80L/ -80LL		-85/-85L/ -85LL		-90/-90L/ -90LL		Unit	Notes
		Min	Max	Min	Max	Min	Max		
Read Cycle Time	t_{RC}	90	—	90	—	90	—	ns	
Chip Enable Access Time	t_{CE}	—	80	—	85	—	90	ns	*1, *3
Output Enable Access Time	t_{OE}	—	45	—	45	—	45	ns	*1
Address Access Time	t_{AA}	—	80	—	85	—	90	ns	*1, *4
Output Data Hold Time	t_{OH}	5	—	5	—	5	—	ns	*1
$\overline{CE1}$ Low to Output Low-Z	t_{CLZ}	5	—	5	—	5	—	ns	*2
$\overline{OE}$ Low to Output Low-Z	t_{OLZ}	0	—	0	—	0	—	ns	*2
$\overline{CE1}$ High to Output High-Z	t_{CHZ}	—	30	—	30	—	30	ns	*2
$\overline{OE}$ High to Output High-Z	t_{OHZ}	—	25	—	25	—	25	ns	*2
Address Setup Time to $\overline{CE1}$ Low	t_{ASC}	-5	—	-5	—	-5	—	ns	*5
Address Setup Time to $\overline{OE}$ Low	t_{ASO}	45	—	45	—	45	—	ns	*3, *6
	$t_{ASO[ABS]}$	10	—	10	—	10	—	ns	*7
Address Invalid Time	t_{AX}	—	5	—	5	—	5	ns	*4
$\overline{CE1}$ Low to Address Hold Time	t_{CLAH}	90	—	90	—	90	—	ns	*4
$\overline{OE}$ Low to Address Hold Time	t_{OLAH}	45	—	45	—	45	—	ns	*4, *8
$\overline{CE1}$ High to Address Hold Time	t_{CHAH}	-5	—	-5	—	-5	—	ns	
$\overline{OE}$ High to Address Hold Time	t_{OHAH}	-5	—	-5	—	-5	—	ns	
$\overline{CE1}$ Low to $\overline{OE}$ Low Delay Time	t_{CLOL}	45	1000	45	1000	45	1000	ns	*3, *6, *8, *9
$\overline{OE}$ Low to $\overline{CE1}$ High Delay Time	t_{OLCH}	45	—	45	—	45	—	ns	*8
$\overline{CE1}$ High Pulse Width	t_{CP}	20	—	20	—	20	—	ns	
$\overline{OE}$ High Pulse Width	t_{OP}	45	1000	45	1000	45	1000	ns	*6, *8, *9
	$t_{OP[ABS]}$	20	—	20	—	20	—	ns	*7

*1: The output load is 30 pF.

*2: The output load is 5 pF.

*3: The t_{CE} is applicable if $\overline{OE}$ is brought to Low before $\overline{CE1}$ goes Low and is also applicable if actual value of both or either t_{ASO} or t_{CLOL} is shorter than specified value.

*4: Applicable only to A_0 and A_1 when both $\overline{CE1}$ and $\overline{OE}$ are kept at Low for the address access.

*5: Applicable if $\overline{OE}$ is brought to Low before $\overline{CE1}$ goes Low.

*6: The t_{ASO} , t_{CLOL} (Min) and t_{OP} (Min) are reference values when the access time is determined by t_{OE} .

If actual value of each parameter is shorter than specified minimum value, t_{OE} become longer by the amount of subtraction actual value from specified minimum value.

For example, if actual t_{ASO} , t_{ASO} (actual), is shorter than specified minimum value, t_{ASO} (Min), during $\overline{OE}$ control access (i.e., $\overline{CE1}$ stays Low), the t_{OE} become t_{OE} (Max) + t_{ASO} (Min) - t_{ASO} (actual).

*7: The $t_{ASO[ABS]}$ and $t_{OP[ABS]}$ is the absolute minimum value during $\overline{OE}$ control access.

*8: If actual value of either t_{CLOL} or t_{OP} is shorter than specified minimum value, both t_{OLAH} and t_{OLCH} become t_{RC} (Min) - t_{CLOL} (actual) or t_{RC} (Min) - t_{OP} (actual).

*9: Maximum value is applicable if $\overline{CE1}$ is kept at Low.

(2) Write Operation

Parameter	Symbol	-80/-80L/ -80LL		-85/-85L/ -85LL		-90/-90L/ -90LL		Unit	Notes
		Min	Max	Min	Max	Min	Max		
Write Cycle Time	t_{WC}	90	—	90	—	90	—	ns	*1
Address Setup Time	t_{AS}	0	—	0	—	0	—	ns	*2
Address Hold Time	t_{AH}	45	—	45	—	45	—	ns	*2
$\overline{CE1}$ Write Setup Time	t_{CS}	0	1000	0	1000	0	1000	ns	
$\overline{CE1}$ Write Hold Time	t_{CH}	0	1000	0	1000	0	1000	ns	
$\overline{WE}$ Setup Time	t_{WS}	0	—	0	—	0	—	ns	
$\overline{WE}$ Hold Time	t_{WH}	0	—	0	—	0	—	ns	
$\overline{LB}$ and $\overline{UB}$ Setup Time	t_{BS}	-5	—	-5	—	-5	—	ns	
$\overline{LB}$ and $\overline{UB}$ Hold Time	t_{BH}	-5	—	-5	—	-5	—	ns	
$\overline{OE}$ Setup Time	t_{OES}	0	1000	0	1000	0	1000	ns	*3
$\overline{OE}$ Hold Time	$t_{OE H}$	45	1000	45	1000	45	1000	ns	*3, *4
	$t_{OE H[ABS]}$	20	—	20	—	20	—	ns	*5
$\overline{OE}$ High to $\overline{CE1}$ Low Setup Time	t_{OHCL}	-3	—	-3	—	-3	—	ns	*6
Address Hold Time to $\overline{OE}$ High	t_{OHAH}	0	—	0	—	0	—	ns	*7
$\overline{CE1}$ Write Pulse Width	t_{CW}	60	—	60	—	60	—	ns	*1, *8
$\overline{WE}$ Write Pulse Width	t_{WP}	60	—	60	—	60	—	ns	*1, *8
$\overline{CE1}$ Write Recovery Time	t_{WRC}	15	—	15	—	15	—	ns	*1, *9
$\overline{WE}$ Write Recovery Time	t_{WR}	15	1000	15	1000	15	1000	ns	*1, *3, *9
Data Setup Time	t_{DS}	20	—	20	—	20	—	ns	
Data Hold Time	t_{DH}	0	—	0	—	0	—	ns	
$\overline{CE1}$ High Pulse Width	t_{CP}	20	—	20	—	20	—	ns	*9

*1: Minimum value must be equal or greater than the sum of actual t_{CW} (or t_{WP}) and t_{WRC} (or t_{WR}) .

*2: New write address is valid from either $\overline{CE1}$ or $\overline{WE}$ is brought to High.

*3: Maximum value is applicable if $\overline{CE1}$ is kept at Low and both $\overline{WE}$ and $\overline{OE}$ are kept at High.

*4: The $t_{OE H}$ is specified from end of t_{WC} (Min) and is a reference value when access time is determined by t_{OE} .
If actual value is shorter than specified minimum value, t_{OE} become longer by the amount of subtracting actual value from specified minimum value.

*5: The $t_{OE H[ABS]}$ is the absolute minimum value if write cycle is terminated by $\overline{WE}$ and $\overline{CE1}$ stays Low.

*6: t_{OHCL} (Min) must be satisfied if read operation is not performed prior to write operation.
In case $\overline{OE}$ is disabled after t_{OHCL} (Min) , $\overline{WE}$ Low must be asserted after t_{RC} (Min) from $\overline{CE1}$ Low.
In other words, read operation is initiated if t_{OHCL} (Min) is not satisfied.

*7: Applicable if $\overline{CE1}$ stays Low after read operation.

*8: t_{CW} and t_{WP} is applicable if write operation is initiated by $\overline{CE1}$ and $\overline{WE}$, respectively.

*9: t_{WRC} and t_{WR} is applicable if write operation is terminated by $\overline{CE1}$ and $\overline{WE}$, respectively.
The t_{WR} (Min) can be ignored if $\overline{CE1}$ is brought to High together or after $\overline{WE}$ is brought to High.
In such case, the t_{CP} (Min) must be satisfied.

(3) Power Down Parameters

Parameter	Symbol	Value		Unit	Note
		Min	Max		
CE2 Low Setup Time for Power Down Entry	t_{CSP}	10	—	ns	
CE2 Low Hold Time after Power Down Entry	t_{C2LP}	100	—	ns	
$\overline{CE1}$ High Hold Time following CE2 High after Power Down Exit	t_{CHH}	350	—	μs	
$\overline{CE1}$ High Setup Time following CE2 High after Power Down Exit	t_{CHS}	10	—	ns	

(4) Other Timing Parameters

Parameter	Symbol	Value		Unit	Note
		Min	Max		
$\overline{CE1}$ High to $\overline{OE}$ Invalid Time for Standby Entry	t_{CHOX}	20	—	ns	
$\overline{CE1}$ High to $\overline{WE}$ Invalid Time for Standby Entry	t_{CHWX}	20	—	ns	*1
CE2 Low Hold Time after Power-up	t_{C2LH}	50	—	μs	*2
CE2 High Hold Time after Power-up	t_{C2HL}	50	—	μs	*3
$\overline{CE1}$ High Hold Time following CE2 High after Power-up	t_{CHH}	350	—	μs	*2
Input Transition Time	t_T	1	25	ns	*4

*1: It may write some data into any address location if t_{CHWX} is not satisfied.

*2: Must satisfy t_{CHH} (Min) after t_{C2LH} (Min) .

*3: Requires Power Down mode entry and exit after t_{C2HL} .

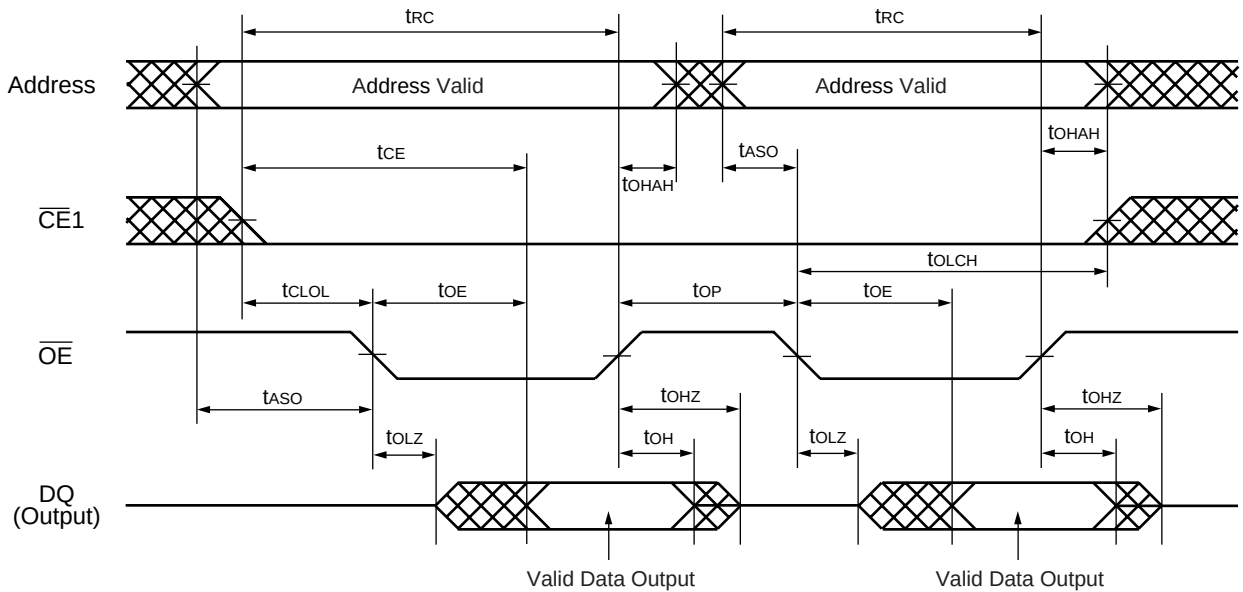
*4: The Input Transition Time (t_T) at AC testing is 5 ns as shown in below. If actual t_T is longer than 5 ns, it may violate some timing parameters of AC specification.

(5) AC Test Conditions

Parameter	Symbol	Conditions	Measured Value	Unit	Note
Input High Level	V_{IH}	$V_{DD} = 3.1 \text{ V to } 3.5 \text{ V}$	2.6	V	
		$V_{DD} = 2.7 \text{ V to } 3.1 \text{ V}$	2.3	V	
		$V_{DD} = 2.3 \text{ V to } 2.7 \text{ V}$	2.0	V	
Input Low Level	V_{IL}	$V_{DD} = 3.1 \text{ V to } 3.5 \text{ V}$	0.5	V	
		$V_{DD} = 2.7 \text{ V to } 3.1 \text{ V}$	0.5	V	
		$V_{DD} = 2.3 \text{ V to } 2.7 \text{ V}$	0.4	V	
Input Timing Measurement Level	V_{REF}	$V_{DD} = 3.1 \text{ V to } 3.5 \text{ V}$	1.5	V	
		$V_{DD} = 2.7 \text{ V to } 3.1 \text{ V}$	1.3	V	
		$V_{DD} = 2.3 \text{ V to } 2.7 \text{ V}$	1.1	V	
Input Transition Time	t_T	Between V_{IL} and V_{IH}	5	ns	

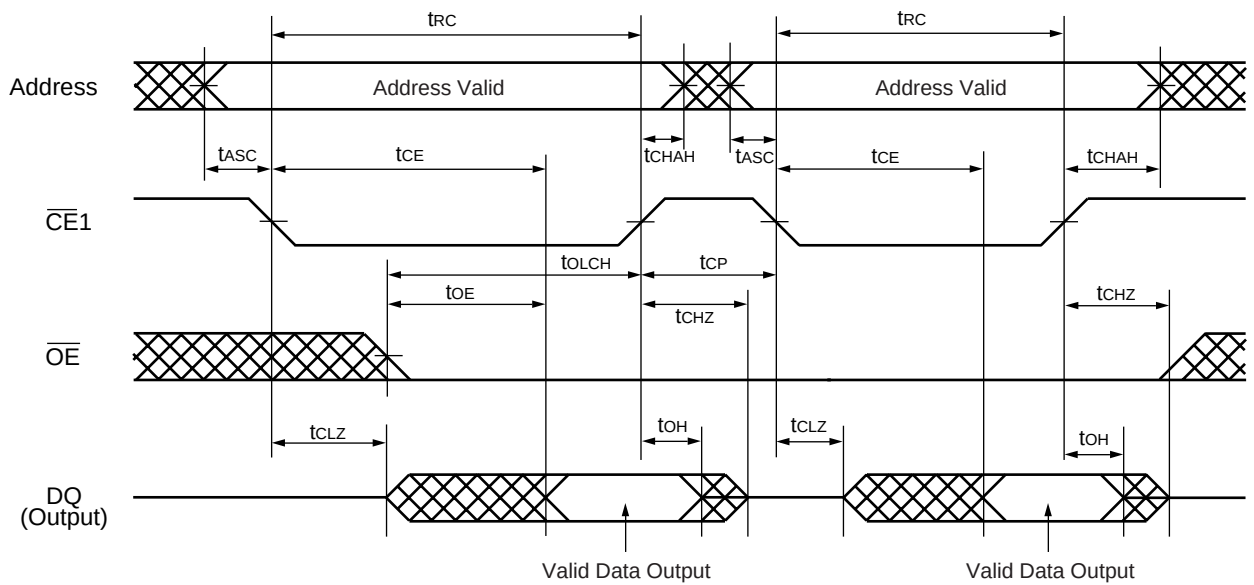
■ TIMING DIAGRAM

1. READ Timing #1 ($\overline{\text{OE}}$ Control Access)



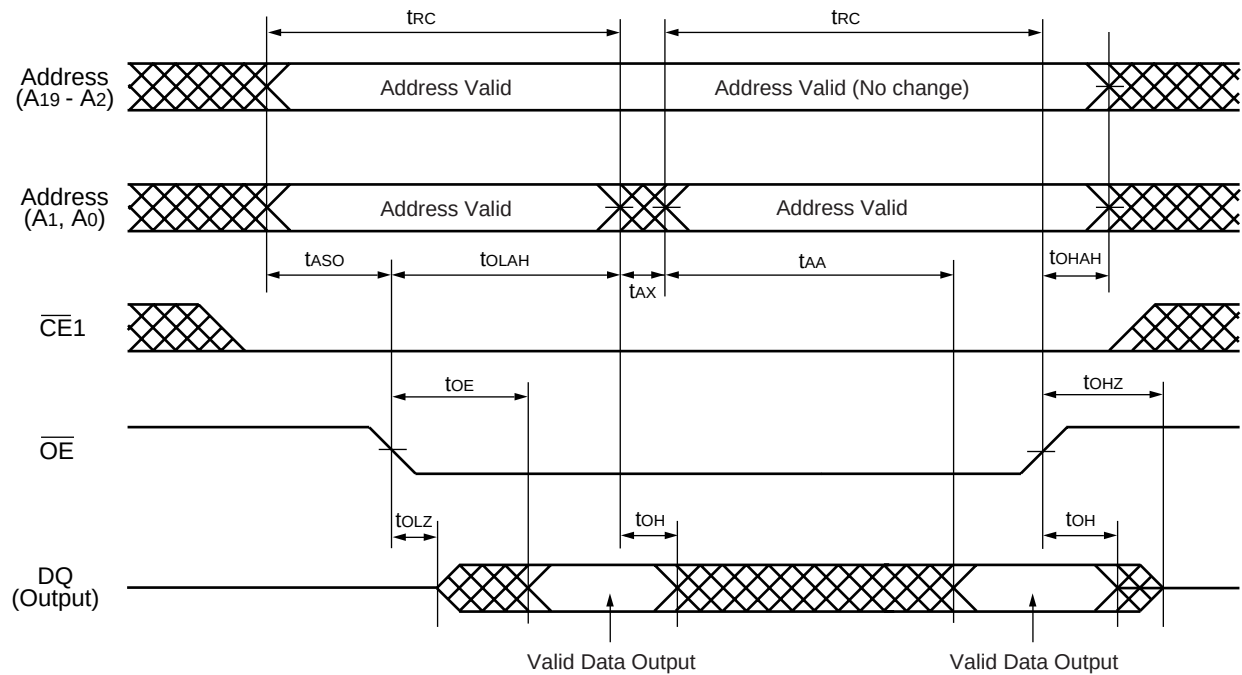
Note : CE2 and $\overline{\text{WE}}$ must be High for entire read cycle.

2. READ Timing #2 ($\overline{\text{CE1}}$ Control Access)



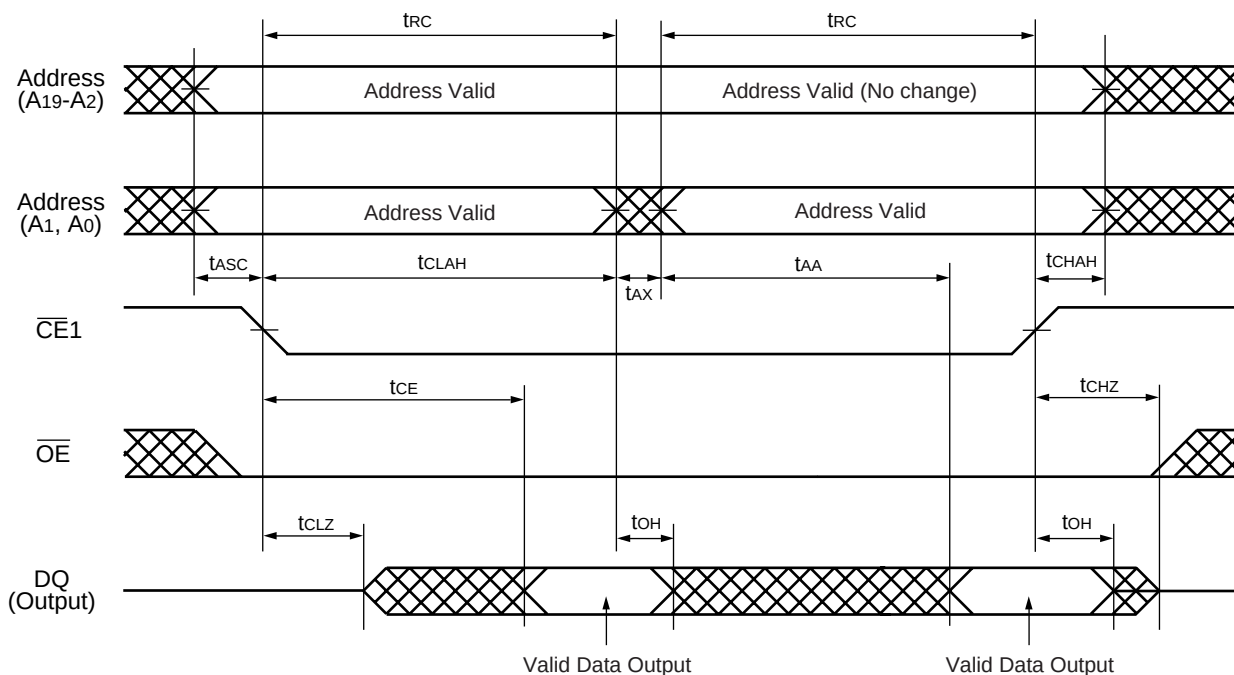
Note : CE2 and $\overline{\text{WE}}$ must be High for entire read cycle.

3. READ Timing #3 (Address Access after $\overline{\text{OE}}$ Control Access)



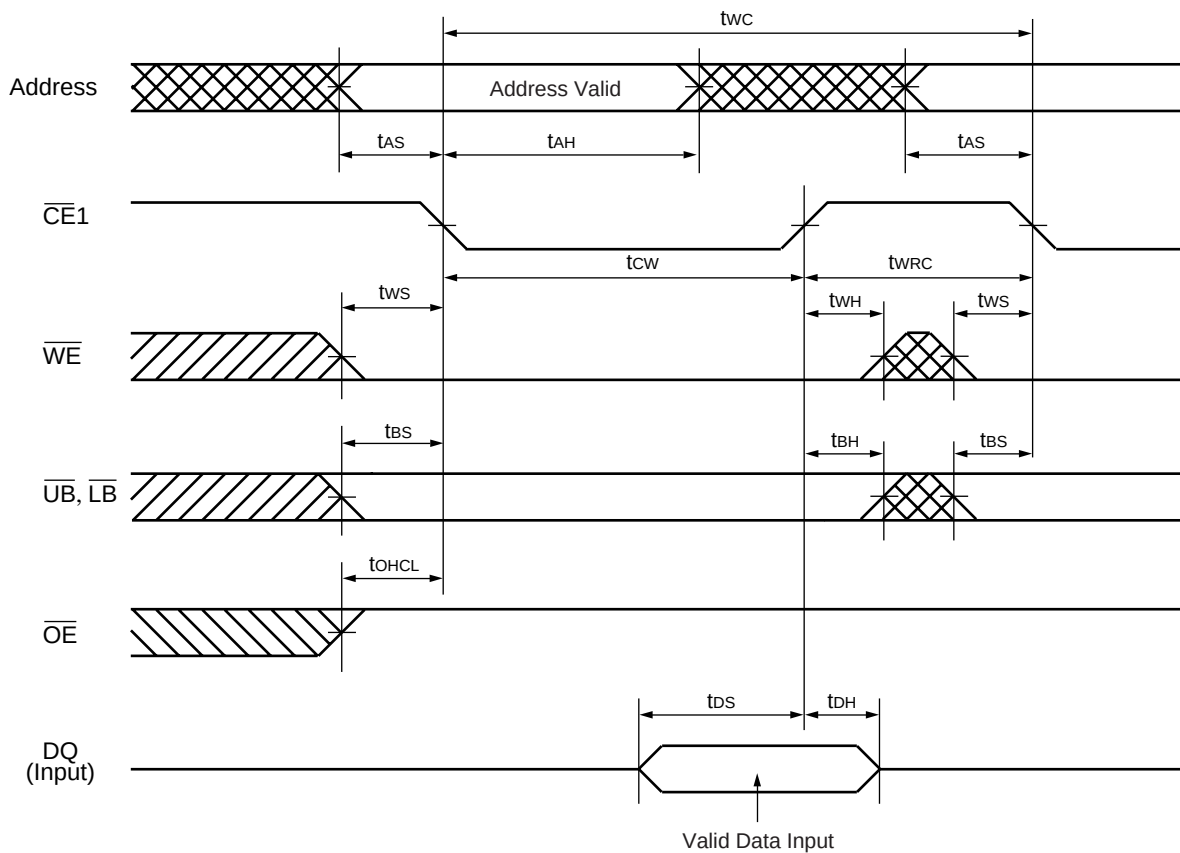
Note : CE2 and $\overline{\text{WE}}$ must be High for entire read cycle.

4. READ Timing #4 (Address Access after $\overline{\text{CE1}}$ Control Access)



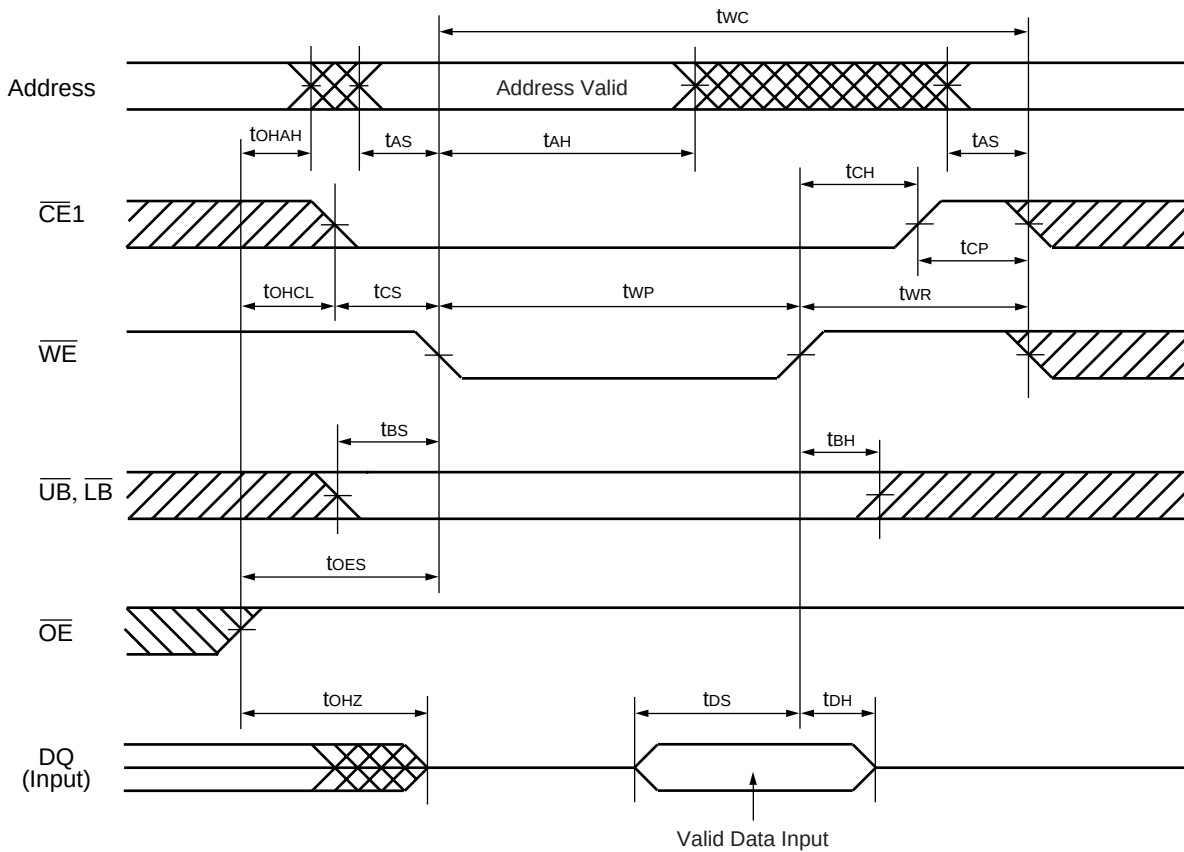
Note : CE2 and $\overline{\text{WE}}$ must be High for entire read cycle.

5. WRITE Timing #1 ($\overline{\text{CE1}}$ Control)

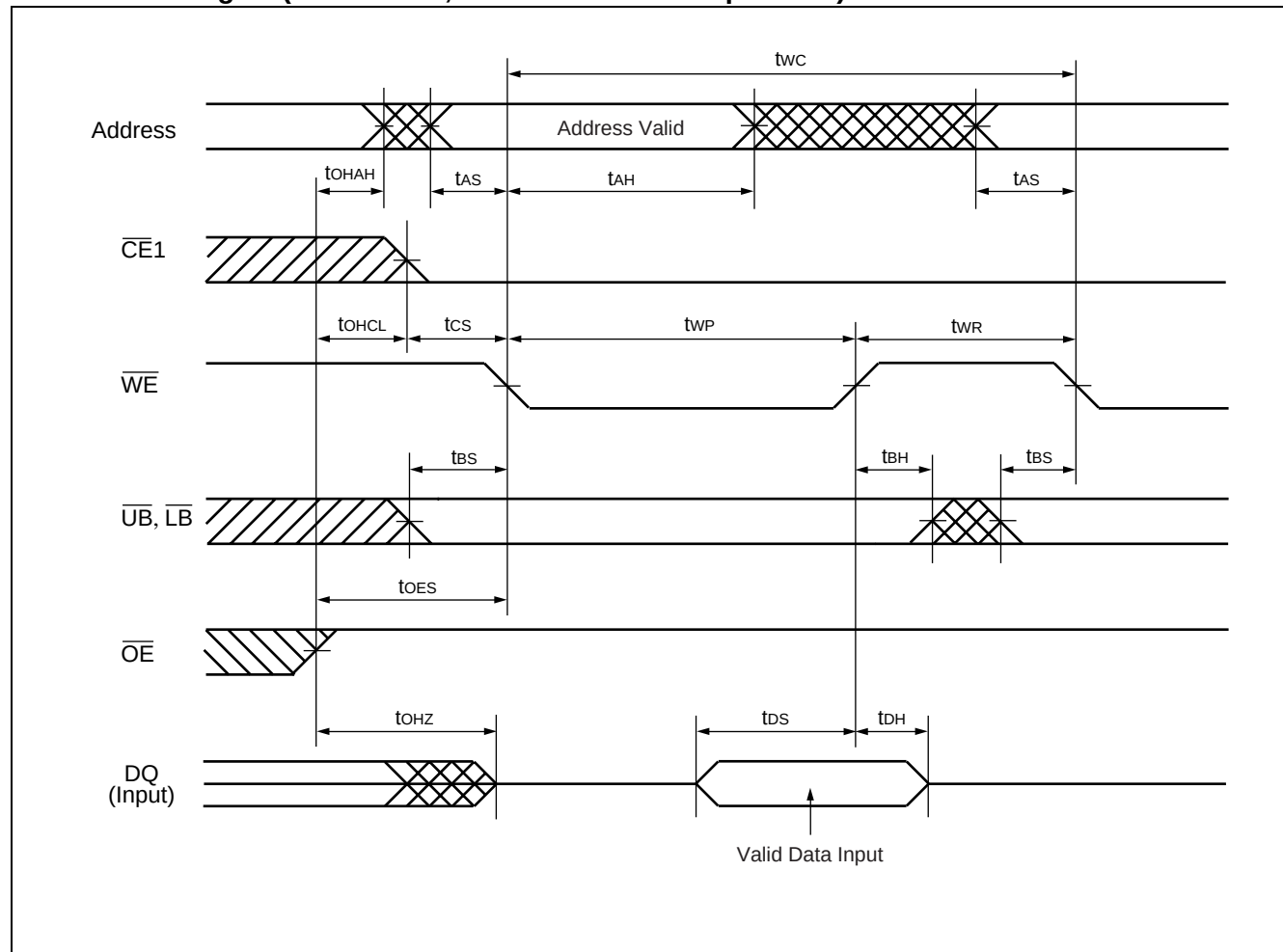


Note : CE2 must be High for write cycle.

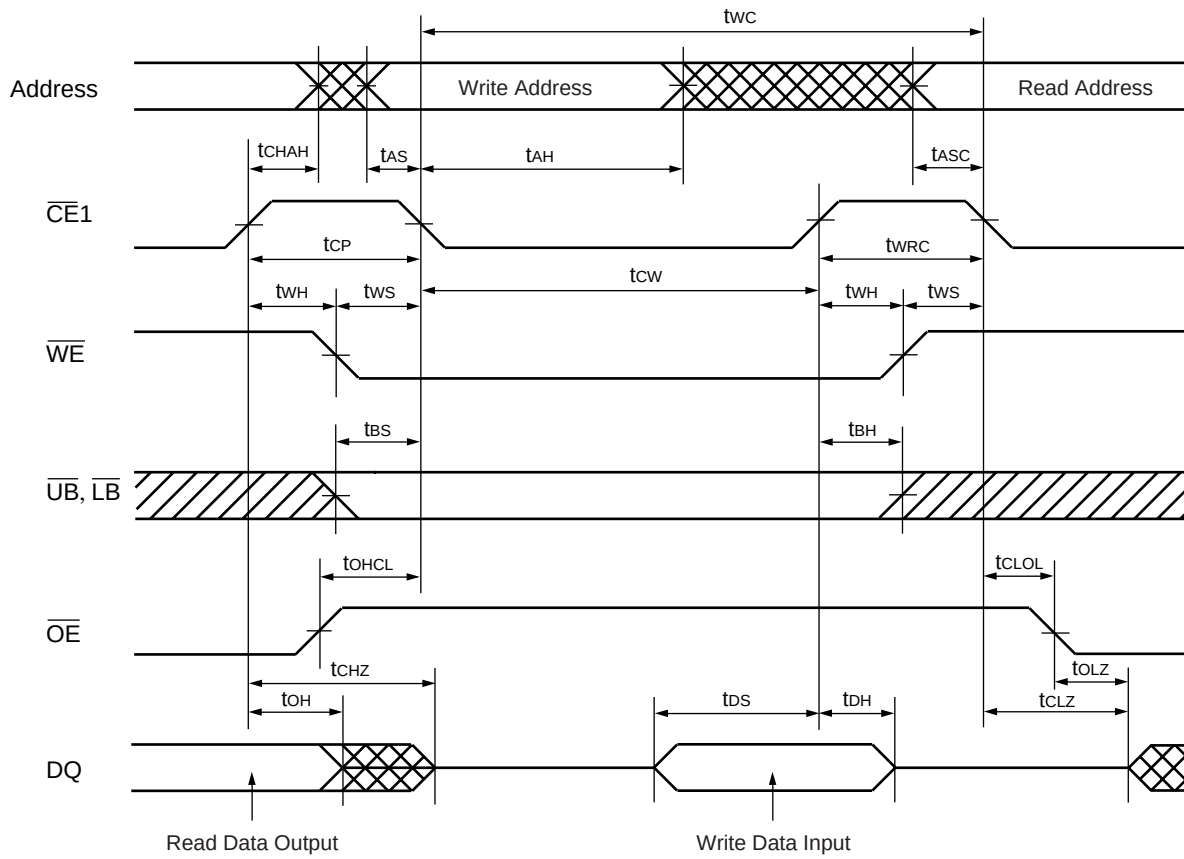
6. WRITE Timing #2-1 ($\overline{\text{WE}}$ Control, Single Write Operation)



7. WRITE Timing #2 ($\overline{\text{WE}}$ Control, Continuous Write Operation)

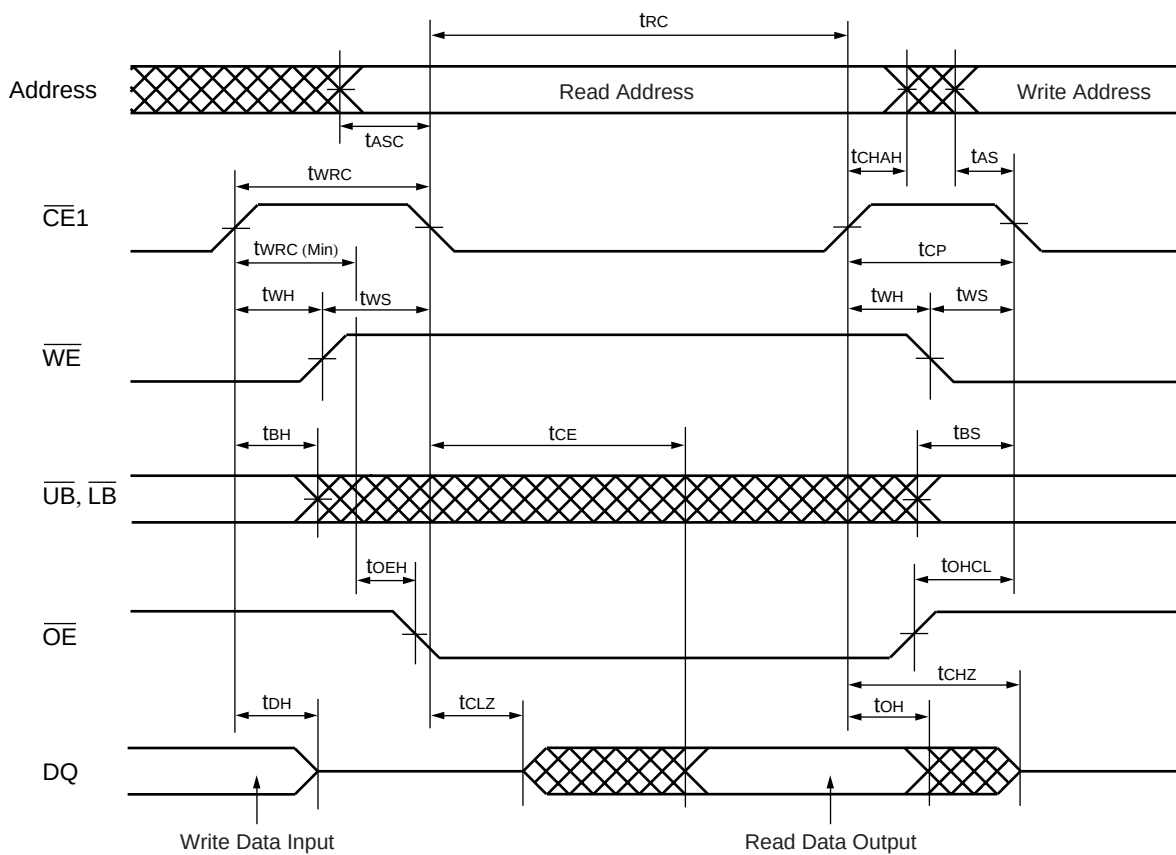


8. READ/WRITE Timing #1-1 ($\overline{\text{CE1}}$ Control)



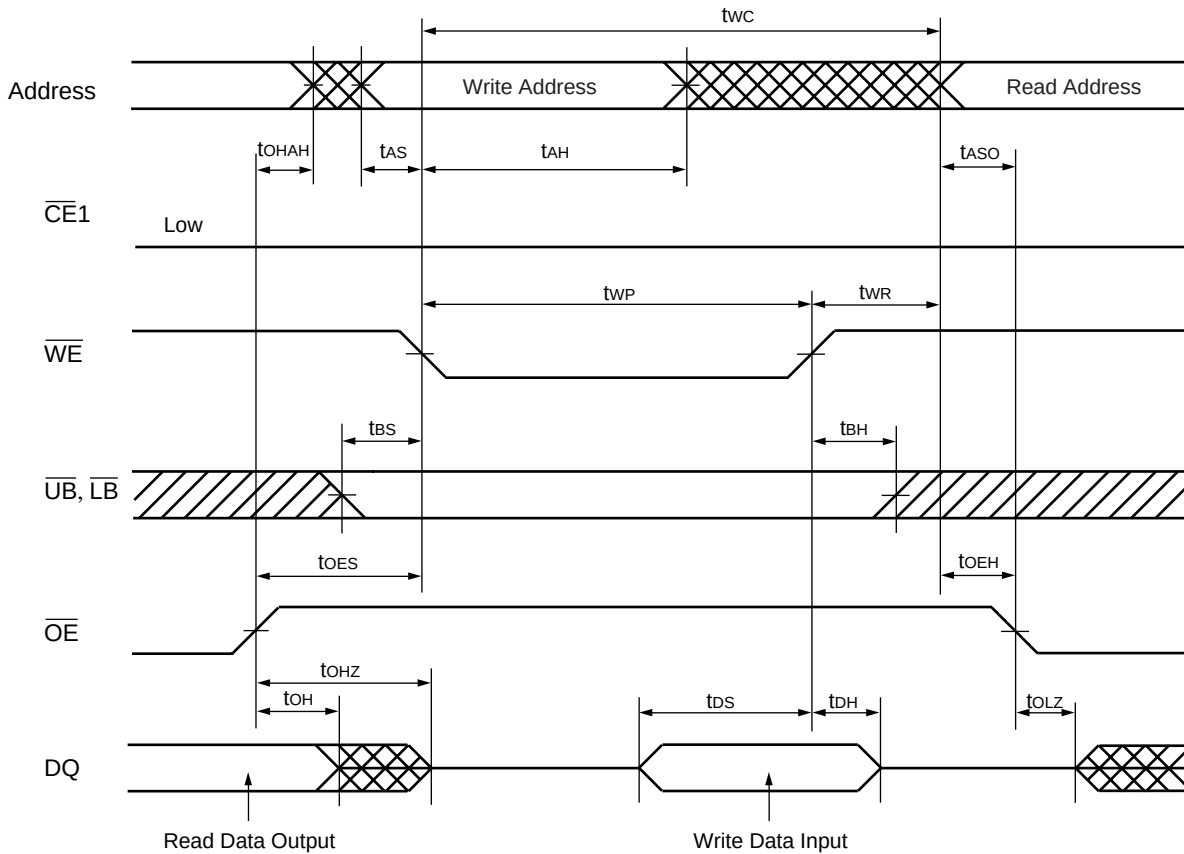
Note : Write address is valid from either $\overline{\text{CE1}}$ or $\overline{\text{WE}}$ of last falling edge.

9. READ/WRITE Timing #1-2 ($\overline{\text{CE1}}$ Control)



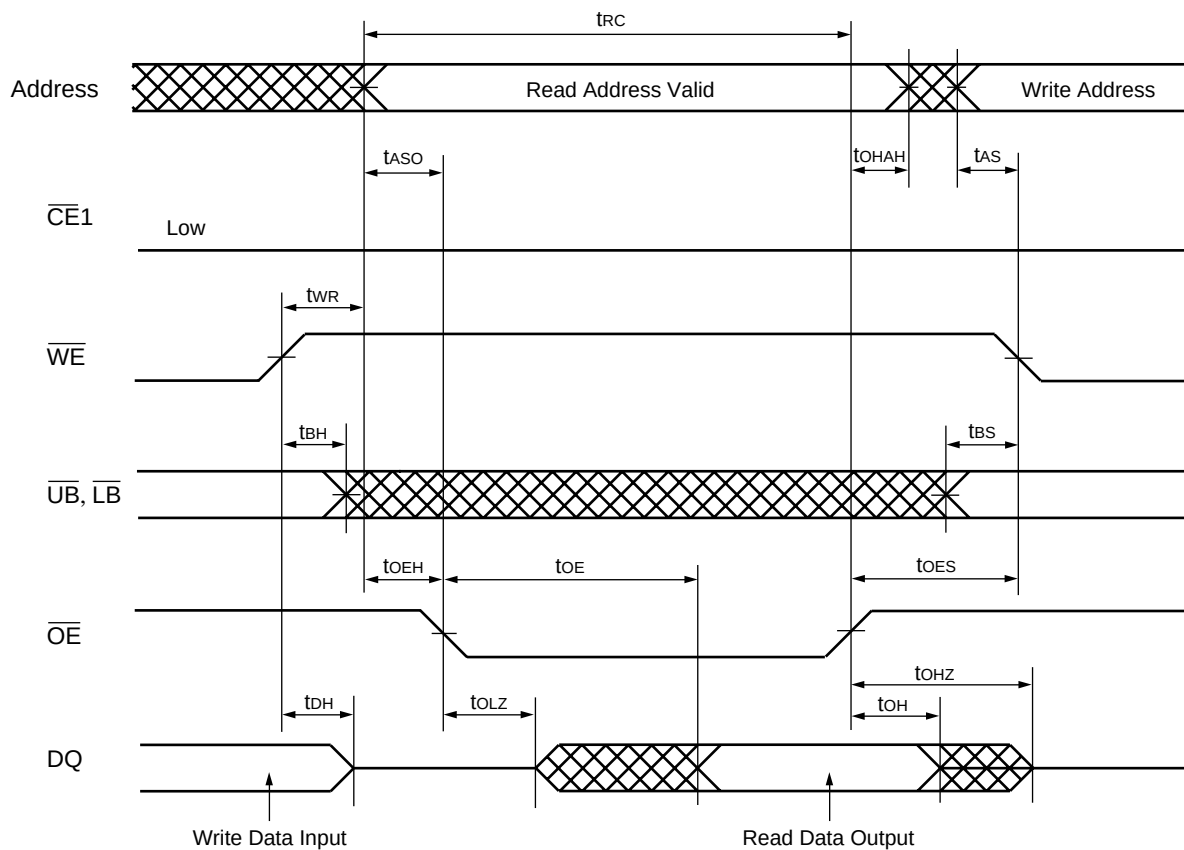
Note : The t_{OEH} is specified from the time satisfied both t_{WRC} and $t_{\text{WR (Min)}}$.

10. READ ($\overline{\text{OE}}$ Control) /WRITE ($\overline{\text{WE}}$ Control) Timing #2-1



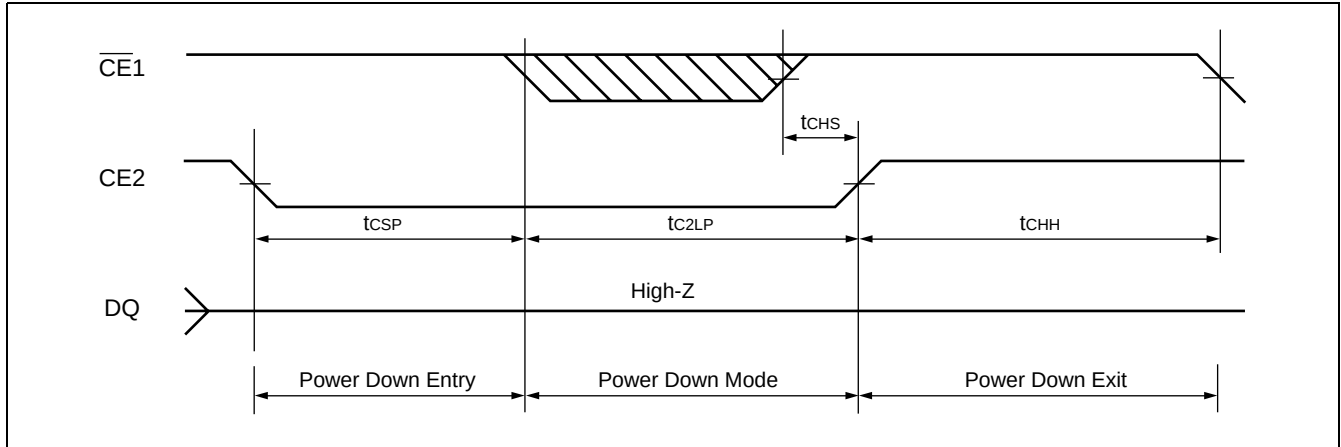
Note : $\overline{\text{CE1}}$ can be tied to Low for $\overline{\text{WE}}$ and $\overline{\text{OE}}$ controlled operation.
When $\overline{\text{CE1}}$ is tied to Low, output is exclusively controlled by $\overline{\text{OE}}$.

11. READ ($\overline{\text{OE}}$ Control) /WRITE ($\overline{\text{WE}}$ Control) Timing #2-2

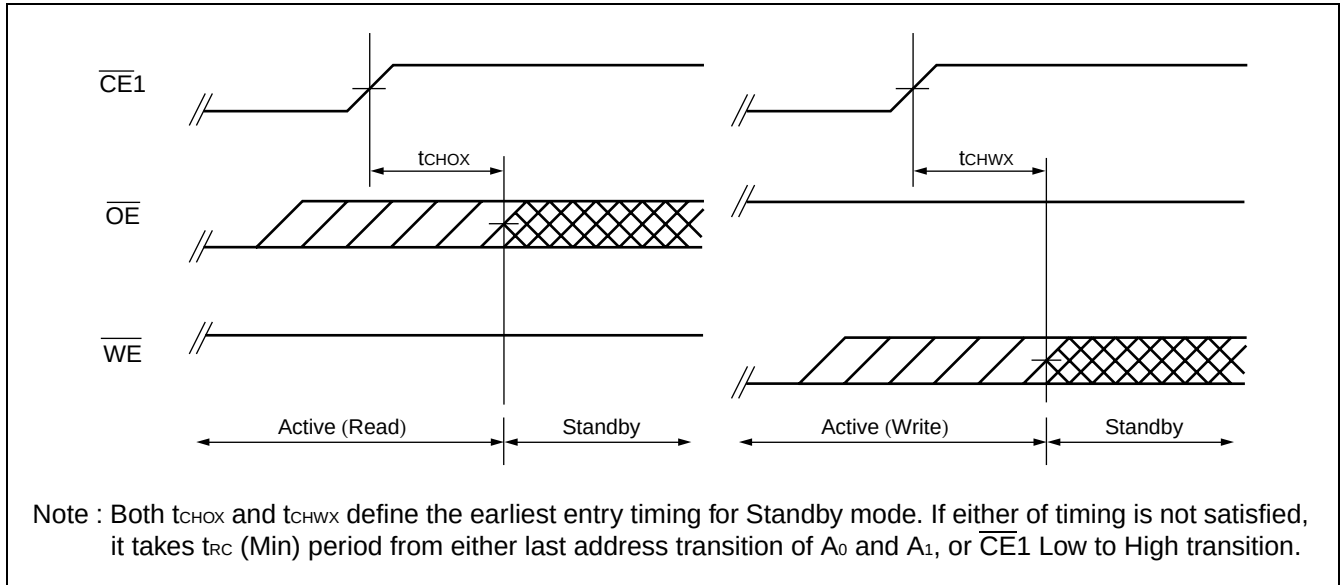


Note : $\overline{\text{CE1}}$ can be tied to Low for $\overline{\text{WE}}$ and $\overline{\text{OE}}$ controlled operation.
When $\overline{\text{CE1}}$ is tied to Low, output is exclusively controlled by $\overline{\text{OE}}$.

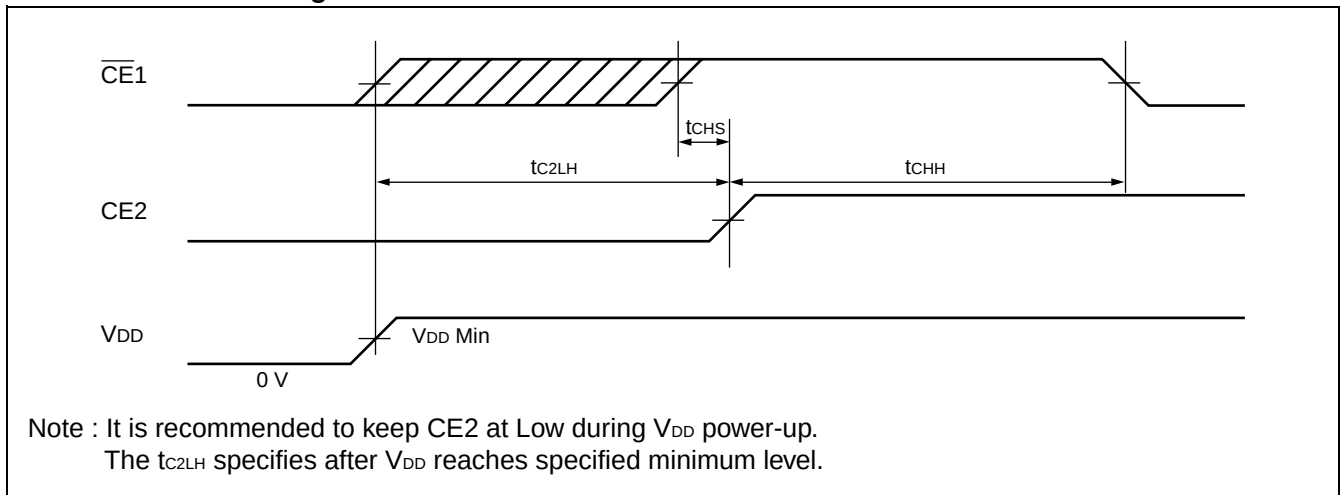
12. POWER DOWN Timing



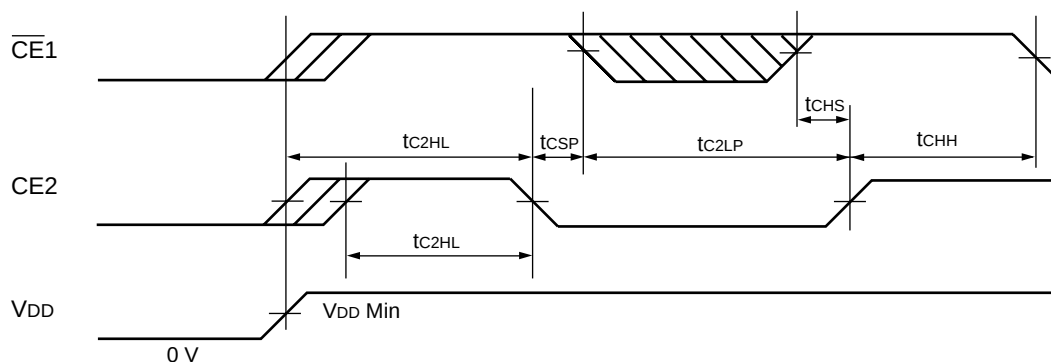
13. Standby Entry Timing after Read or Write



14. POWER-UP Timing 1



15. POWER-UP Timing 2



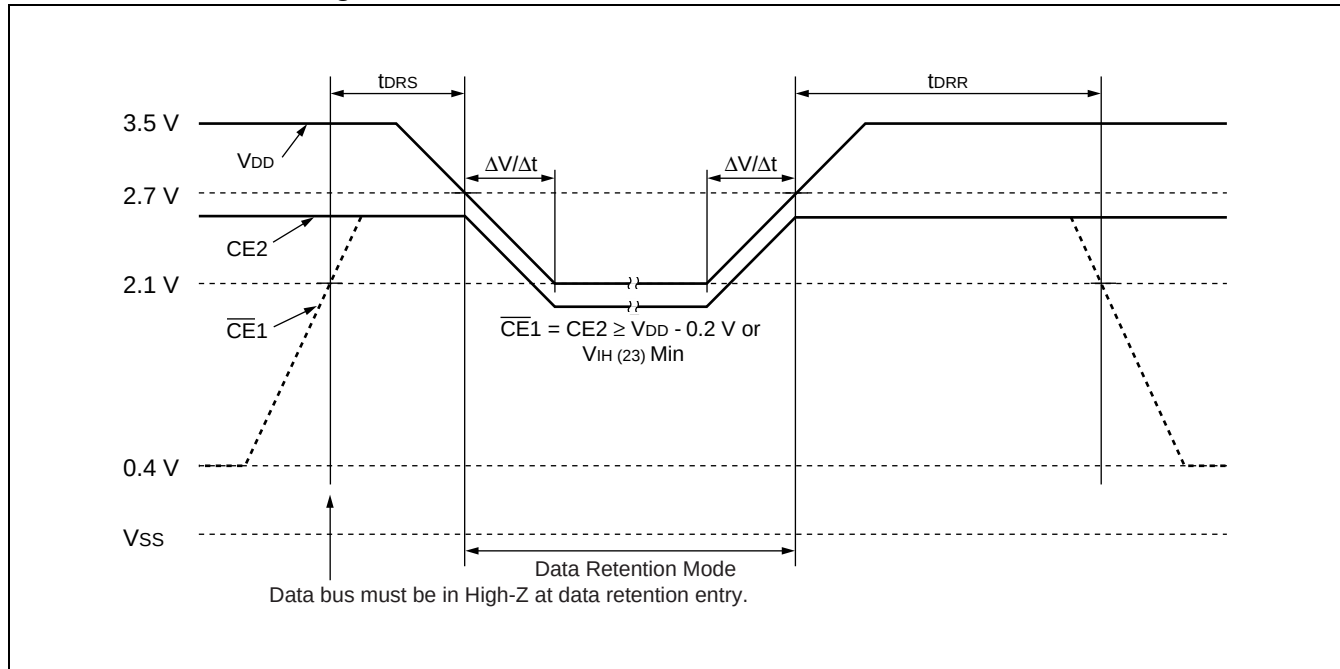
Note : The t_{C2HL} specifies from CE2 Low to High transition after V_{DD} reaches specified minimum level.
 $\overline{CE1}$ must be brought to High prior to or together with CE2 Low to High transition.

■ DATA RETENTION

1. Low V_{DD} Characteristics

Parameter	Symbol	Test Conditions	Value		Unit
			Min	Max	
V_{DD} Data Retention Supply Voltage	V_{DR}	$\overline{CE1} = CE2 \geq V_{DD} - 0.2 \text{ V}$ or, $\overline{CE1} = CE2 = V_{IH}$,	2.1	3.5	V
V_{DD} Data Retention Supply Current	L Version	$V_{DD} = V_{DD(23)}$, $V_{IN} = V_{IH(23)}$ or V_{IL} $\overline{CE1} = CE2 = V_{IH(23)}$, $I_{OUT} = 0 \text{ mA}$	—	5	mA
			—	1.5	
			—	1	
	LL Version	$V_{DD} = V_{DD(23)}$, $V_{IN} \leq 0.2 \text{ V}$ or $V_{IN} \geq V_{DD} - 0.2 \text{ V}$, $\overline{CE1} = CE2 \geq V_{DD} - 0.2 \text{ V}$, $I_{OUT} = 0 \text{ mA}$	—	200	μA
			—	100	
			—	70	
Data Retention Setup Time	t_{DRS}	$V_{DD} = V_{DD(27)}$ at data retention entry	0	—	ns
Data Retention Recovery Time	t_{DRR}	$V_{DD} = V_{DD(27)}$ after data retention	90	—	ns
V_{DD} Voltage Transition Time	$\Delta V/\Delta t$	—	0.5	—	V/ μs

2. Data Retention Timing



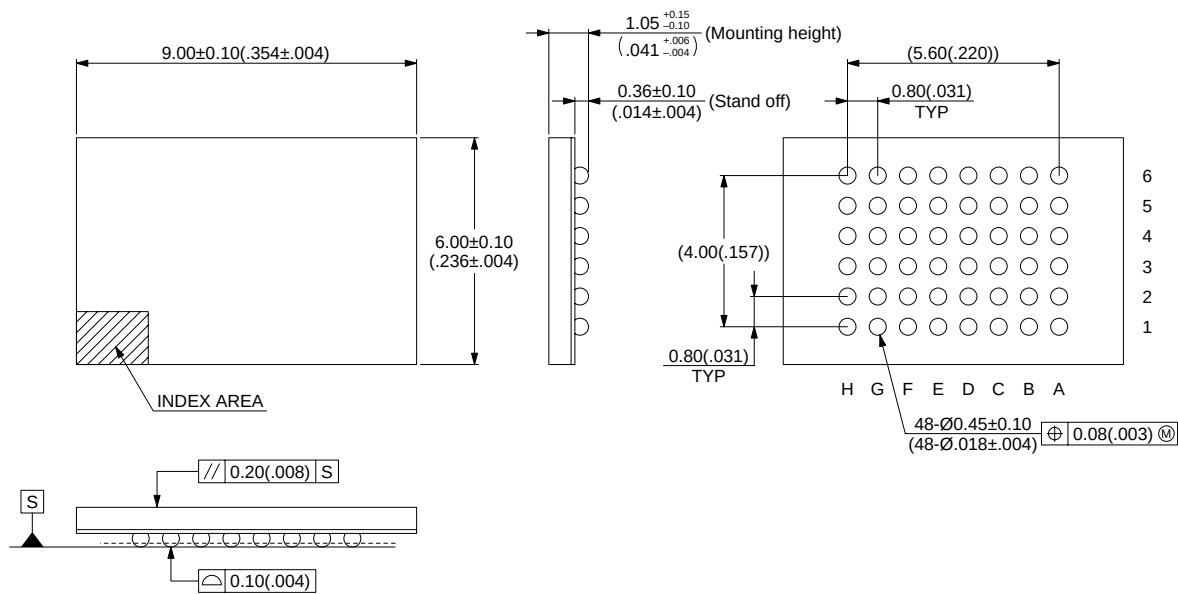
MB82D01171A-80/80L/80LL/85/85L/85LL/90/90L/90LL

■ ORDERING INFORMATION

Part Number	Package	Remarks
MB82D01171A-80PBT	48-ball plastic FBGA 0.8 mm pitch (BGA-48P-M16)	$t_{CE} = 80 \text{ ns Max}$, $I_{DD S1} = 200 \mu\text{A Max}$ Flash Compatible Package
MB82D01171A-80LPBT	48-ball plastic FBGA 0.8 mm pitch (BGA-48P-M16)	$t_{CE} = 80 \text{ ns Max}$, $I_{DD S1} = 100 \mu\text{A Max}$ Flash Compatible Package
MB82D01171A-80LLPBT	48-ball plastic FBGA 0.8 mm pitch (BGA-48P-M16)	$t_{CE} = 80 \text{ ns Max}$, $I_{DD S1} = 70 \mu\text{A Max}$ Flash Compatible Package
MB82D01171A-85PBT	48-ball plastic FBGA 0.8 mm pitch (BGA-48P-M16)	$t_{CE} = 85 \text{ ns Max}$, $I_{DD S1} = 200 \mu\text{A Max}$ Flash Compatible Package
MB82D01171A-85LPBT	48-ball plastic FBGA 0.8 mm pitch (BGA-48P-M16)	$t_{CE} = 85 \text{ ns Max}$, $I_{DD S1} = 100 \mu\text{A Max}$ Flash Compatible Package
MB82D01171A-85LLPBT	48-ball plastic FBGA 0.8 mm pitch (BGA-48P-M16)	$t_{CE} = 85 \text{ ns Max}$, $I_{DD S1} = 70 \mu\text{A Max}$ Flash Compatible Package
MB82D01171A-90PBT	48-ball plastic FBGA 0.8 mm pitch (BGA-48P-M16)	$t_{CE} = 90 \text{ ns Max}$, $I_{DD S1} = 200 \mu\text{A Max}$ Flash Compatible Package
MB82D01171A-90LPBT	48-ball plastic FBGA 0.8 mm pitch (BGA-48P-M16)	$t_{CE} = 90 \text{ ns Max}$, $I_{DD S1} = 100 \mu\text{A Max}$ Flash Compatible Package
MB82D01171A-90LLPBT	48-ball plastic FBGA 0.8 mm pitch (BGA-48P-M16)	$t_{CE} = 90 \text{ ns Max}$, $I_{DD S1} = 70 \mu\text{A Max}$ Flash Compatible Package
MB82D01171A-80PBN	48-ball plastic FBGA 0.75 mm pitch (BGA-48P-M18)	$t_{CE} = 80 \text{ ns Max}$, $I_{DD S1} = 200 \mu\text{A Max}$ SRAM Compatible Package
MB82D01171A-80LPBN	48-ball plastic FBGA 0.75 mm pitch (BGA-48P-M18)	$t_{CE} = 80 \text{ ns Max}$, $I_{DD S1} = 100 \mu\text{A Max}$ SRAM Compatible Package
MB82D01171A-80LLPBN	48-ball plastic FBGA 0.75 mm pitch (BGA-48P-M18)	$t_{CE} = 80 \text{ ns Max}$, $I_{DD S1} = 70 \mu\text{A Max}$ SRAM Compatible Package
MB82D01171A-85PBN	48-ball plastic FBGA 0.75 mm pitch (BGA-48P-M18)	$t_{CE} = 85 \text{ ns Max}$, $I_{DD S1} = 200 \mu\text{A Max}$ SRAM Compatible Package
MB82D01171A-85LPBN	48-ball plastic FBGA 0.75 mm pitch (BGA-48P-M18)	$t_{CE} = 85 \text{ ns Max}$, $I_{DD S1} = 100 \mu\text{A Max}$ SRAM Compatible Package
MB82D01171A-85LLPBN	48-ball plastic FBGA 0.75 mm pitch (BGA-48P-M18)	$t_{CE} = 85 \text{ ns Max}$, $I_{DD S1} = 70 \mu\text{A Max}$ SRAM Compatible Package
MB82D01171A-90PBN	48-ball plastic FBGA 0.75 mm pitch (BGA-48P-M18)	$t_{CE} = 90 \text{ ns Max}$, $I_{DD S1} = 200 \mu\text{A Max}$ SRAM Compatible Package
MB82D01171A-90LPBN	48-ball plastic FBGA 0.75 mm pitch (BGA-48P-M18)	$t_{CE} = 90 \text{ ns Max}$, $I_{DD S1} = 100 \mu\text{A Max}$ SRAM Compatible Package
MB82D01171A-90LLPBN	48-ball plastic FBGA 0.75 mm pitch (BGA-48P-M18)	$t_{CE} = 90 \text{ ns Max}$, $I_{DD S1} = 70 \mu\text{A Max}$ SRAM Compatible Package

■ PACKAGE DIMENSIONS

48-ball plastic FBGA
(BGA-48P-M16)



© 2000 FUJITSU LIMITED B48016S-1c-1

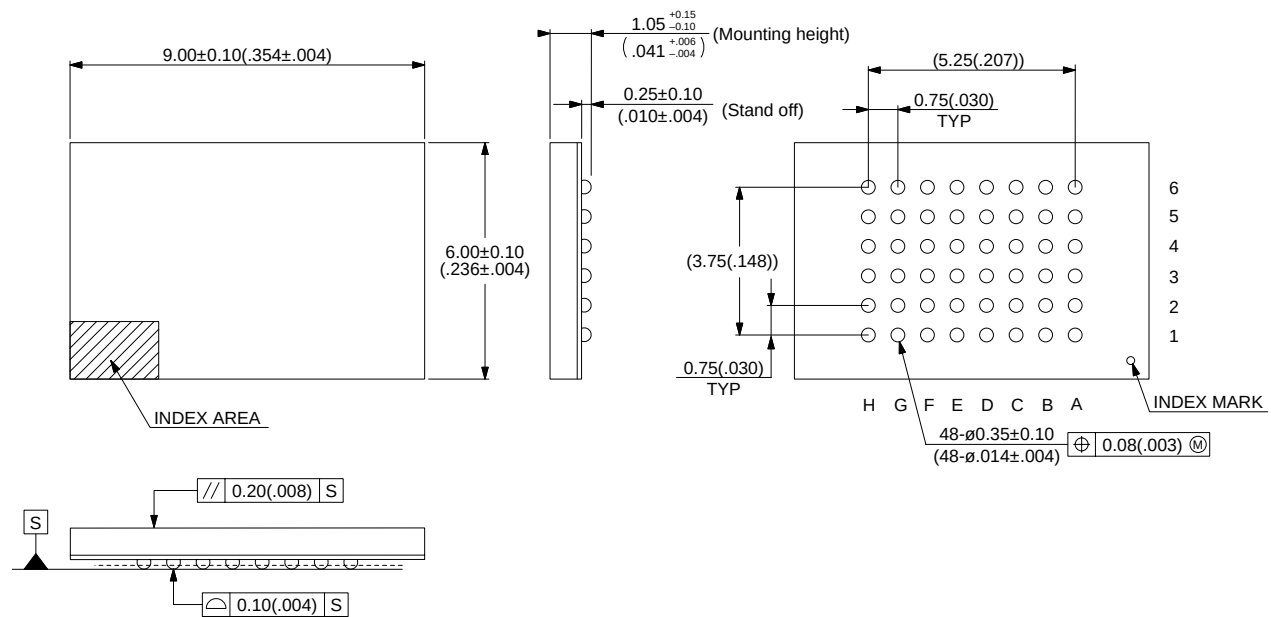
Dimensions in mm (inches)

(Continued)

MB82D01171A-80/80L/80LL/85/85L/85LL/90/90L/90LL

(Continued)

48-ball plastic FBGA
(BGA-48P-M18)



© 2001 FUJITSU LIMITED B48018S-c-1-1

Dimensions in mm (inches)

FUJITSU LIMITED

All Rights Reserved.

The contents of this document are subject to change without notice. Customers are advised to consult with FUJITSU sales representatives before ordering.

The information and circuit diagrams in this document are presented as examples of semiconductor device applications, and are not intended to be incorporated in devices for actual use. Also, FUJITSU is unable to assume responsibility for infringement of any patent rights or other rights of third parties arising from the use of this information or circuit diagrams.

The products described in this document are designed, developed and manufactured as contemplated for general use, including without limitation, ordinary industrial use, general office use, personal use, and household use, but are not designed, developed and manufactured as contemplated (1) for use accompanying fatal risks or dangers that, unless extremely high safety is secured, could have a serious effect to the public, and could lead directly to death, personal injury, severe physical damage or other loss (i.e., nuclear reaction control in nuclear facility, aircraft flight control, air traffic control, mass transport control, medical life support system, missile launch control in weapon system), or (2) for use requiring extremely high reliability (i.e., submersible repeater and artificial satellite).

Please note that Fujitsu will not be liable against you and/or any third party for any claims or damages arising in connection with above-mentioned uses of the products.

Any semiconductor devices have an inherent chance of failure. You must protect against injury, damage or loss from such failures by incorporating safety design measures into your facility and equipment such as redundancy, fire protection, and prevention of over-current levels and other abnormal operating conditions.

If any products described in this document represent goods or technologies subject to certain restrictions on export under the Foreign Exchange and Foreign Trade Law of Japan, the prior authorization by Japanese government will be required for export of those products from Japan.

F0112

© FUJITSU LIMITED Printed in Japan



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.